



26N50

Preliminary

Power MOSFET

26A, 500V N-CHANNEL
POWER MOSFET

DESCRIPTION

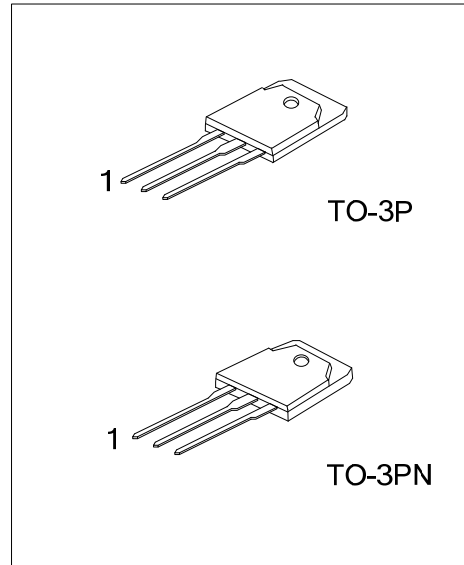
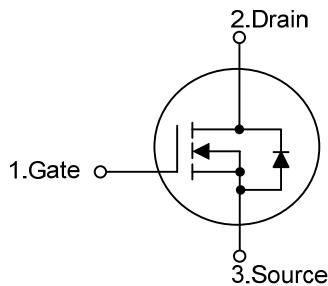
The UTC **26N50** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **26N50** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} \leq 0.24\Omega$ @ $V_{GS}=10V, I_D=13A$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL



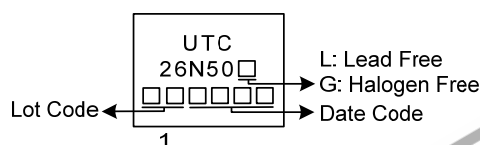
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
26N50L-T3P-T	26N50G-T3P-T	TO-3P	G	D	S	Tube
26N50L-T3N-T	26N50G-T3N-T	TO-3PN	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>26N50G-T3P-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) T3P: TO-3P, T3N: TO-3PN</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
---	--

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_c=25^\circ\text{C}$)	I_D	26 (Note 2)	A
	Pulsed (Note 3)	I_{DM}	96 (Note 2)	A
Avalanche Current (Note 3)		I_{AR}	26	A
Avalanche Energy	Single Pulsed (Note 4)	E_{AS}	1100	mJ
	Repetitive (Note 5)	E_{AR}	29	mJ
Peak Diode Recovery dv/dt (Note 5)		dv/dt	15	V/ns
Power Dissipation		P_D	290	W
Derate above 25°C			2.33	$W/^\circ\text{C}$
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Drain current limited by maximum junction temperature.
3. Repetitive Rating: Pulse width limited by maximum junction temperature.
4. $L = 3.4\text{mH}$, $I_{AS} = 26\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
5. $I_{SD} \leq 26\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	40	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.43	$^\circ\text{C}/\text{W}$

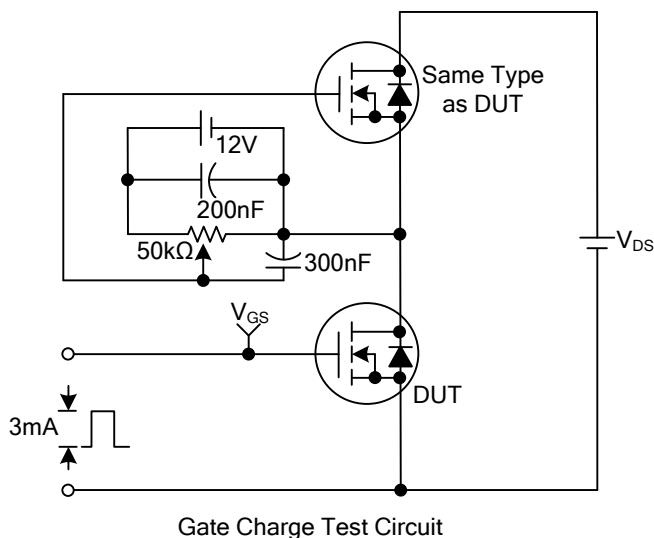
■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$			50	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=13\text{A}$		0.15	0.24	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		3500	4500	pF
Output Capacitance	C_{OSS}			520	670	pF
Reverse Transfer Capacitance	C_{RSS}			55	70	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{GS}=10\text{V}$, $V_{DS}=400\text{V}$, $I_D=26\text{A}$ (Note 1, 2)		90	120	nC
Gate to Source Charge	Q_{GS}			23		nC
Gate to Drain Charge	Q_{GD}			52		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250\text{V}$, $I_D=26\text{A}$, $R_G=25\Omega$ (Note 1, 2)		80	170	ns
Rise Time	t_R			250	500	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			200	400	ns
Fall-Time	t_F			155	320	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				24	A
Maximum Body-Diode Pulsed Current	I_{SM}				96	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=26\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=26\text{A}$, $V_{GS}=0\text{V}$,		250		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$di_f/dt=100\text{A}/\mu\text{s}$ (Note 1)		1.1		μC

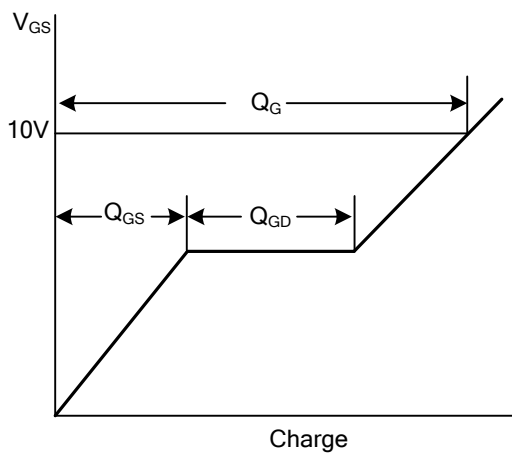
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

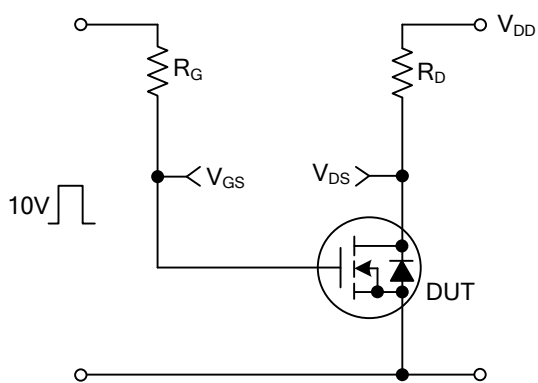
■ TEST CIRCUITS AND WAVEFORMS



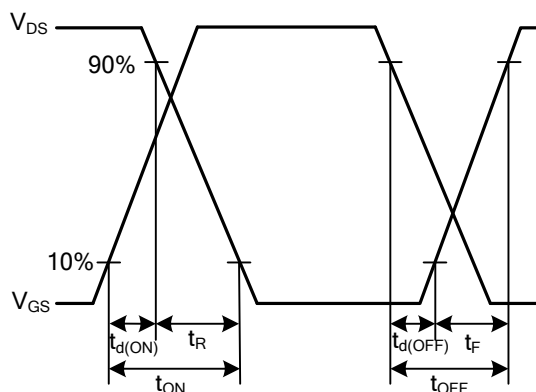
Gate Charge Test Circuit



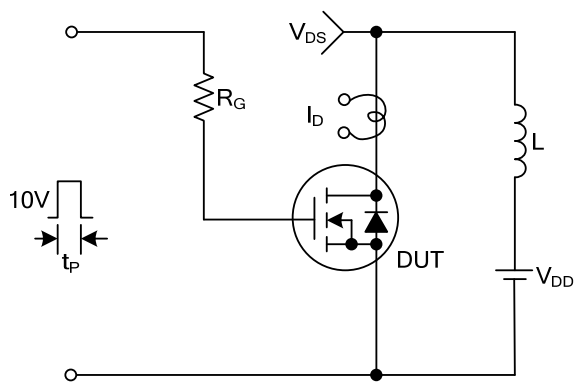
Gate Charge Waveforms



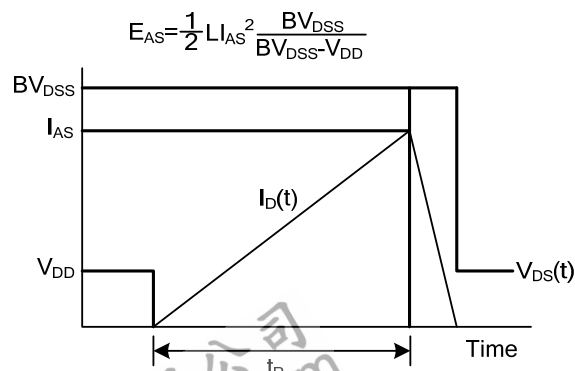
Resistive Switching Test Circuit



Resistive Switching Waveforms



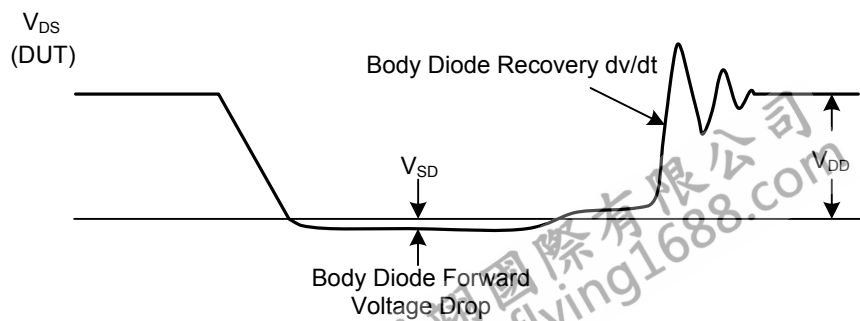
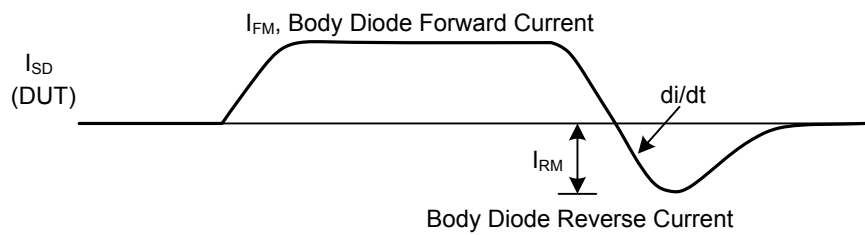
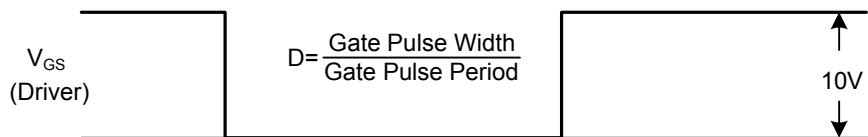
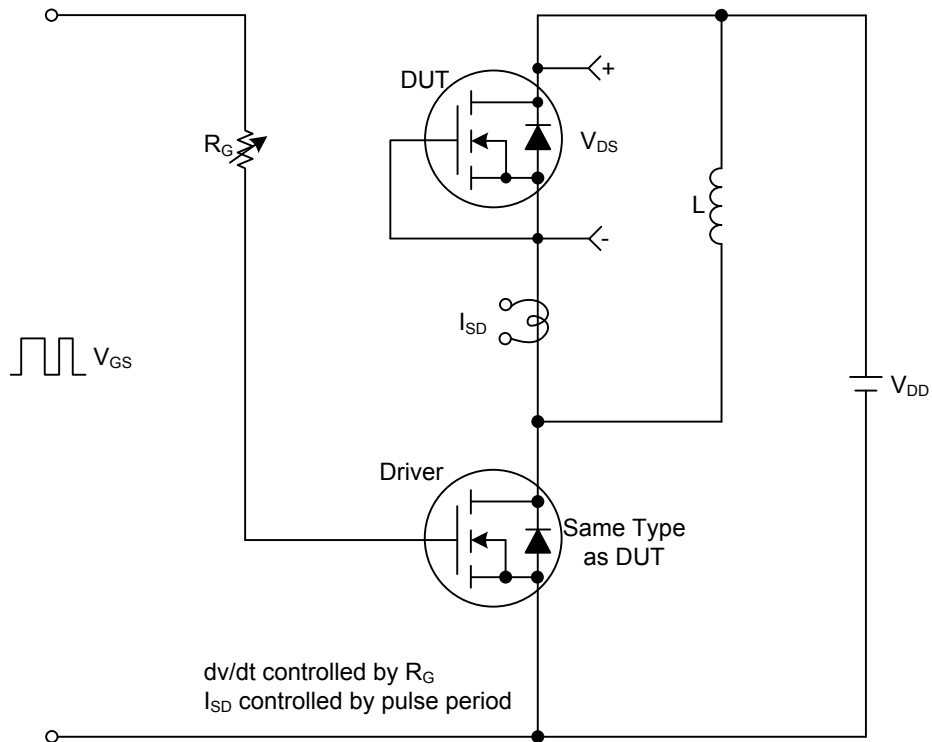
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TEST CIRCUITS AND WAVEFORMS(Cont.)

Peak Diode Recovery dv/dt Test Circuit & Waveforms



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.